

# Feng Wei

## List of Publications by Year in descending order

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26  
papers

907  
citations

687363

13  
h-index

552781

26  
g-index

26  
all docs

26  
docs citations

26  
times ranked

1960  
citing authors

#	ARTICLE	IF	CITATIONS
1	Influence of the hard masks profiles on formation of nanometer Si scalloped fins arrays. <i>Microelectronic Engineering</i> , 2018, 198, 48-54.	2.4	11
2	High mechanical endurance RRAM based on amorphous gadolinium oxide for flexible nonvolatile memory application. <i>Journal Physics D: Applied Physics</i> , 2015, 48, 205104.	2.8	17
3	Nonvolatile Electrochemical Metallization Memory Based on Nanocrystalline La <sub>2</sub> O <sub>3</sub> Solid Electrolyte Thin Film. <i>IEEE Journal of the Electron Devices Society</i> , 2015, 3, 254-259.	2.1	7
4	Chemical vapor deposition growth and transport properties of MoS <sub>2</sub> thin layers using molybdenum and sulfur as precursors. <i>Rare Metals</i> , 2015, , 1.	7.1	8
5	Interaction of Gd and N incorporation on the band structure and oxygen vacancies of HfO <sub>2</sub> gate dielectric films. <i>Physica Status Solidi (B): Basic Research</i> , 2014, 251, 1635-1638.	1.5	6
6	Highly Transparent Dysprosium Oxide-Based RRAM With Multilayer Graphene Electrode for Low-Power Nonvolatile Memory Application. <i>IEEE Transactions on Electron Devices</i> , 2014, 61, 1388-1393.	3.0	26
7	NH <sub>2</sub> CH <sub>3</sub> NH <sub>2</sub> PbI <sub>3</sub> : An Alternative Organolead Iodide Perovskite Sensitizer for Mesoscopic Solar Cells. <i>Chemistry of Materials</i> , 2014, 26, 1485-1491.	6.7	516
8	Enhancing the efficiency of TiO <sub>2</sub> -perovskite heterojunction solar cell via evaporating Cs <sub>2</sub> CO <sub>3</sub> on TiO <sub>2</sub> . <i>Physica Status Solidi - Rapid Research Letters</i> , 2014, 8, 912-916.	2.4	12
9	Resistive switching behaviour of highly epitaxial CeO <sub>2</sub> thin film for memory application. <i>Physica Status Solidi - Rapid Research Letters</i> , 2014, 8, 95-99.	2.4	18
10	The enhancement of unipolar resistive switching behavior via an amorphous TiO <sub>x</sub> layer formation in Dy <sub>2</sub> O <sub>3</sub> -based forming-free RRAM. <i>Solid-State Electronics</i> , 2013, 89, 12-16.	1.4	15
11	Selected-control hydrothermal synthesis and photoresponse properties of Bi <sub>2</sub> S <sub>3</sub> micro/nanocrystals. <i>CrystEngComm</i> , 2013, 15, 6611.	2.6	45
12	Effects of NH <sub>3</sub> annealing on interface and electrical properties of Gd-doped HfO <sub>2</sub> /Si stack. <i>Journal of Rare Earths</i> , 2013, 31, 395-399.	4.8	13
13	Epitaxial growth and characterization of Gd <sub>2</sub> O <sub>3</sub> -doped HfO <sub>2</sub> film on Ge (001) substrates with zero interface layer. <i>Journal of Rare Earths</i> , 2013, 31, 1092-1095.	4.8	2
14	Epitaxial growth and electrical properties of ultrathin La <sub>2</sub> Hf <sub>2</sub> O <sub>7</sub> high-k gate dielectric films. <i>Applied Surface Science</i> , 2013, 283, 554-558.	6.1	11
15	Characteristics and mechanism of nano-polycrystalline La <sub>2</sub> O <sub>3</sub> thin film resistance switching memory. <i>Physica Status Solidi - Rapid Research Letters</i> , 2013, 7, 1005-1008.	2.4	25
16	Atomic configuration of the interface between epitaxial Gd doped HfO <sub>2</sub> high k thin films and Ge (001) substrates. <i>Journal of Applied Physics</i> , 2012, 111, .	2.5	6
17	Epitaxy growth and electrical properties of La <sub>2</sub> Hf <sub>2</sub> O <sub>7</sub> thin film on Si(001) substrate by pulsed laser deposition. <i>Journal of Physics: Conference Series</i> , 2009, 152, 012003.	0.4	5
18	Twin-free (111)-oriented epitaxial Nd <sub>2</sub> Hf <sub>2</sub> O <sub>7</sub> thin films on Ge(111) for high-k dielectrics. <i>Journal Physics D: Applied Physics</i> , 2009, 42, 185301.	2.8	13

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19	Cube-on-cube epitaxy of Gd <sub>2</sub> O <sub>3</sub> -doped HfO <sub>2</sub> films on Si(100) substrates by pulse laser deposition. Journal of Crystal Growth, 2009, 312, 41-43.	1.5	12
20	Effect of (Ba+Sr/Ti) ratio on the dielectric properties for highly (111) oriented (Ba,Sr)TiO <sub>3</sub> thin films. Journal of Alloys and Compounds, 2009, 475, 827-831.	5.5	18
21	Phase control of magnetron sputtering deposited Gd <sub>2</sub> O <sub>3</sub> thin films as high- $\epsilon_r$ gate dielectrics. Journal of Rare Earths, 2008, 26, 371-374.	4.8	20
22	Temperature dependence of thin films growth on Si(001) substrates by pulsed laser deposition. Journal of Crystal Growth, 2008, 310, 4065-4068.	1.5	6
23	Epitaxial La <sub>2</sub> Hf <sub>2</sub> O <sub>7</sub> thin films on Si(001) substrates grown by pulsed laser deposition for high-k gate dielectrics. Applied Physics Letters, 2008, 92, .	3.3	20
24	Epitaxial growth of HfO <sub>2</sub> doped CeO <sub>2</sub> thin films on Si(001) substrates for high- $\epsilon_r$ application. Applied Physics Letters, 2008, 92, 012915.	3.3	9
25	Fabrication and electrical properties of (111) textured (Ba <sub>0.6</sub> Sr <sub>0.4</sub> )TiO <sub>3</sub> film on platinized Si substrate. Applied Physics Letters, 2007, 90, 042905.	3.3	25
26	Solvothermal Growth of Single-Crystal Bismuth Sulfide Nanorods using Bismuth Particles as Source Material. Crystal Growth and Design, 2006, 6, 1942-1944.	3.0	41